

SELECTED ITEM DRAWING



1 GHz to 11 GHz,
Low Noise Amplifier

Unless otherwise
specified
DIMENSIONS ARE
IN INCHES (MM)

TOLERANCES:
.XX +/- 0.010
.XXX +/- 0.005
.XXXX +/- 0.002
ANGLES +/- .5 DEG

Drawing
practices
per **ASME**
Y14.100

SIZE
A

DRAWING NUMBER
SID000066

SID000066 **Rev. B**
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1. SCOPE

1.1. Scope

This drawing establishes the requirements for the 1 GHz to 11 GHz, GaAs, HEMT, MMIC, Low Noise Amplifier, assembled hermetically in the LH250 package, to be screened in accordance with MIL-PRF-38535, Class Level S, to the requirements specified in 4.1, 4.2, and 4.3 herein.

1.2. Analog Devices Part Number

Generic Part Number

ADH753S

Screened Part Number

HMC8356LH250

2. APPLICABLE DOCUMENTS

2.1. Government Documents

Unless otherwise specified, the following drawings and standards, of the issue in effect on the date of the accepted purchase order, in the Department of Defense Index of Specifications and Standards (DODISS) and supplement thereto, shall form a part of this drawing to the extent specified herein.

DEPARTMENT OF DEFENSE TEST METHOD STANDARD

MIL-STD-883

Microcircuits

DEPARTMENT OF DEFENSE PERFORMANCE SPECIFICATIONS

MIL-PRF-38535

Integrated Circuits (Microcircuits) Manufacturing, General Specification For

2.2. Non-Government Documents

The following documents, of the issue in effect on the date of the purchase order, form a part of this drawing to the extent specified herein:

Analog Devices Inc.

[ADI Standard Space Products Program](#) – ASD-*Lite*.

HMC753LP4E Data Sheet

Commercial Product Datasheet

v03.1111 (Reference Only)

3. REQUIREMENTS

3.1. General Requirements

The devices delivered shall comply to this specification.

3.2. Design Construction and Physical Dimensions

The design construction and physical dimensions shall be as defined in Figure 1 herein.

3.3. Traceability

Each delivered device shall be traceable to the wafer lot and wafer number. Inspection lot records shall be maintained to provide traceability to the specific wafer and wafer lot from which the chips originated as well as traceability to package and materials.

3.4. Burn-In and Life Test Circuit

The burn-in and life test circuit and conditions shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test methods 1005 and 1015 per MIL-STD-883.

4. QUALITY ASSURANCE PROVISIONS

4.1. Wafer Lot Acceptance Testing

The wafer lot acceptance testing shall consist of Class Level S inspections per MIL-STD-883 TM 5007.

4.2. Flight Screening Requirements

Flight screening requirements shall be per MIL-STD-883 TM 5004 for Class level S microcircuits.

4.2.1. Electrical Test Requirements

Electrical test requirements are defined in Table I herein.

4.2.2. Electrical Performance Characteristics

Electrical performance characteristics are specified on Table II herein.

4.2.3. Burn-In Delta Requirements

Pre and Post Burn-In Electrical test and delta parameters shall consist of the tests specified in Table III herein.

4.3. Quality Conformance Inspection (QCI)

Group B and Group D tests shall be performed per MIL-STD-883 TM 5005 for Class level S microcircuits.

4.3.1. Post Steady State Life Electrical Test

Post steady state life electrical tests shall consist of the tests specified per Table II tested at room temperature only.

Devices must meet delta parameter requirements in accordance with Table III herein.

5. MIL-PRF-38535 ASD-LITE EXCEPTIONS

The manufacturing flow described in the ADI STANDARD SPACE PRODUCTS PROGRAM is to be considered a part of this specification.

5.1. Wafer Fabrication

Foundry information is available upon request.

5.2. Flight Screening Flow

Reverse Bias Burn-In: Not applicable.

5.3. Group B

Subgroup 2: Resistance to solvents is not applicable.

5.4. Group D

Subgroup 5: Not applicable.

Subgroup 7: Not applicable.

Subgroup 8: Not applicable.

Subgroup 9: Not applicable.

6. PREPARATION FOR DELIVERY

The preparation for delivery, packaging, preservation, ESD protection and handling shall be in accordance with MIL-PRF-38535.

6.1. Part Marking

Devices shall be marked as specified on Figure 1 herein.

6.2. Inspection Data Requirements

The following data shall accompany each shipment.

- a. A Certificate of Conformance (C of C) certifies that the lot(s) meets all requirements of this specification.
- b. Wafer Lot Acceptance data including photos from SEM Inspection defined in 4.1 herein.
- c. Summary of electrical test requirements defined in 4.2 herein.
- d. Summary of QCI results defined in 4.3 herein.
- e. Failure Analysis with photos (If applicable)
- f. A cover sheet indicating the following purchasing information:
 1. Customer purchase order number.
 2. Analog Devices part number.
 3. Part lot identification codes.
 4. Date & quantity shipped.

TABLE I: ELECTRICAL TEST REQUIREMENTS

Test Requirement	Subgroups (in accordance with MIL-PRF-38535, Table III)
Interim Electrical Parameters	1, 4
Final Electrical Parameters	1, 4 <u>1/2/</u>
Group A Electrical Parameters	1, 2, 3, 4, 5, 6
Group B End-Point Electrical Parameters	1, 4 <u>2/</u>
Group D End-Point Electrical Parameters	1, 4

TABLE I Notes:

1/ PDA applies to Table I subgroup 1 and Table III delta parameters.

2/ See Table III for delta parameters

TABLE II: ELECTRICAL PERFORMANCE CHARACTERISTICS (-5 °C, +25 °C AND +70 °C)

Parameter	Test Conditions <u>1/2/3/6/</u> Unless otherwise specified	Group A Subgroups	Limits		Units
			Min	Max	
Small Signal Gain	3 GHz – 8 GHz	4, 5, 6	14		dB
	8 GHz – 10.5 GHz	4, 5, 6	11		dB
Small Signal Gain Flatness	3 GHz – 8 GHz	4, 5, 6		3	dB
	8 GHz – 10.5 GHz	4, 5, 6		3	dB
Gain Variation over Temperature <u>4/</u>	3 GHz – 8 GHz	5, 6		0.01	dB/°C
	8 GHz – 10.5 GHz	5, 6		0.013	dB/°C
Input Return Loss	3 GHz – 8 GHz	4, 5, 6	8		dB
	8 GHz – 10.5 GHz	4, 5, 6	6		dB
Output Return Loss	3 GHz – 8 GHz	4, 5, 6	10		dB
	8 GHz – 10.25 GHz	4, 5, 6	8		dB
	10.5 GHz	4, 5, 6	7		dB
Output Power for 1 dB Compression (OP1dB) <u>5/</u>	3 GHz – 8 GHz	4, 5, 6	13		dBm
	8 GHz – 10.5 GHz	4, 5, 6	11		dBm
Supply Current (Idd)	Small Signal at RFIN	1, 2, 3		60	mA

TABLE II Notes:

1/ Test limits apply between -5 °C and +70 °C with Vdd = +5 V, Vgg2 = +1.5 V.

2/ S-parameter testing performed between 3 GHz and 11 GHz. Data shall be tabulated at

3/ Pre Burn-in data shall be tabulated at 3 GHz, 4 GHz, 5 GHz, 8 GHz, 9 GHz, and 10.5 GHz.

Post Burn-in and final electrical data shall be tabulated at 3 GHz, 4 GHz, 5 GHz, 8 GHz, 9 GHz, 10 GHz, 10.25 GHz, and 10.5 GHz.

4/ Tested at final electrical test only.

5/ OP1dB shall be tested at 3 GHz, 5 GHz, 8 GHz, and 10.5 GHz.

6/ Adjust Vgg1 between -1.4 V and 0 V (typical = -0.8 V) to achieve supply current (Idd) = 55 mA.

TABLE III: BURN-IN/LIFE TEST DELTA LIMITS 1/2/3/4/5/

Parameter	Test Conditions	Delta Limits	Units
Small Signal Gain	Per Table II	± 1	dB
Supply Current (Idd)		± 10	%

TABLE III Notes:

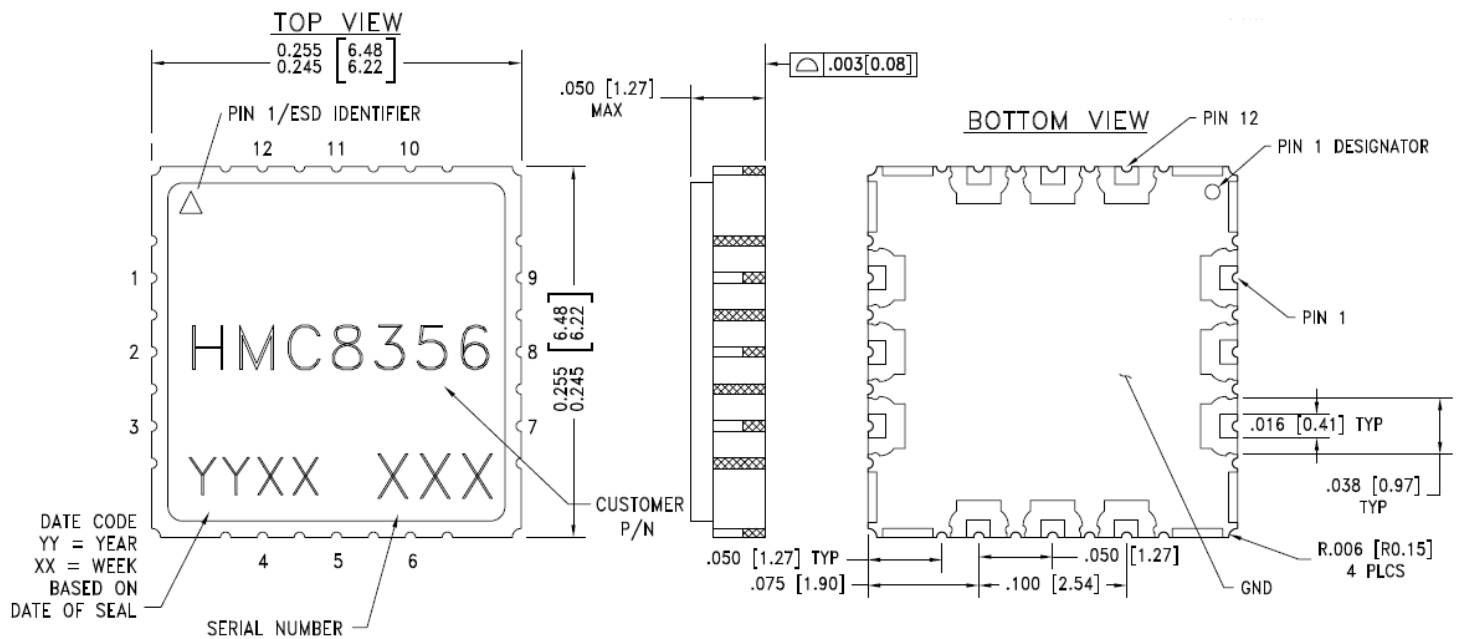
1/ Delta test is performed at $T_A = +25\text{ }^{\circ}\text{C}$ only.

2/ Table II limits will not be exceeded.

3/ Vgg1 voltage set to pre burn-in value for each device.

4/ Delta applies at 3 GHz and 10.5 GHz only

5/ Deltas calculated at pre/post 240 hours and post 240 hour / post1000 hours.



NOTES:

1. PACKAGE BODY MATERIAL: CERAMIC & KOVAR
2. LEAD AND GROUND PADDLE PLATING: GOLD 40-80 MICROINCHES.
3. DIMENSIONS ARE IN INCHES [MILLIMETERS].
4. LEAD SPACING TOLERANCE IS NON-CUMULATIVE.
5. CHARACTERS TO BE LASER MARKED WITH .018"MIN to .030"MAX HEIGHT REQUIREMENTS. UTILIZE MAXIMUM CHARACTER HEIGHT BASED ON LID DIMENSIONS AND BEST FIT. LOCATE APPROX. AS SHOWN.
6. PAD BURR LENGTH 0.15mm MAX. PAD BURR HEIGHT 0.25mm MAX.
7. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.
8. THE SOLDER FILLET BETWEEN PACKAGE AND COVER IS PART OF THE DESIGN SEAL AREA.

PIN #	FUNCTION	PIN #	FUNCTION	PIN #	FUNCTION	PIN #	FUNCTION
1	GND	4	VGG2	7	GND	10	GND
2	RFIN	5	VGG1	8	RFOUT	11	GND
3	GND	6	VDD	9	GND	12	GND

Average Weight: 0.25 grams

Figure 1 – Device Outline for the HMC8356LH250

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option
HMC8356LH250	–5 °C to +70 °C	12-Lead Ceramic Leadless Chip Carrier	LH250 (E-12-6)

Revision History

Revision History		
Rev	Description of Change	Date
A	Initial release.	01/15/2025
B	Update Table II and Figure 1.	09/10/2025